











CSD13202Q2

SLPS313A - SEPTEMBER 2013-REVISED JANUARY 2018

CSD13202Q2 12-V N-Channel NexFET™ Power MOSFETs

Features

- Ultra-Low Q_g and Q_{gd}
- Low Thermal Resistance
- Avalanche Rated
- Lead-Free Terminal Plating
- **RoHS Compliant**
- Halogen Free
- SON 2-mm x 2-mm Plastic Package

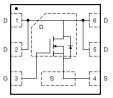
Applications

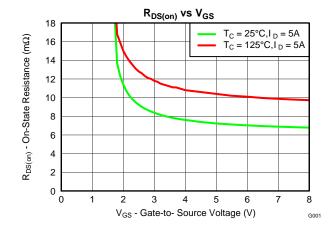
- Optimized for Load Switch Applications
- Storage, Tablets, and Handheld Devices
- Optimized for Control FET Applications
- Point of Load Synchronous Buck Converters

Description

This 12-V, 7.5-mΩ NexFET™ power MOSFET has been designed to minimize losses in power conversion and load management applications. The SON 2 x 2 offers excellent thermal performance for the size of the package.







Product Summary

$T_A = 25^\circ$	С	TYPICAL VA	UNIT	
V_{DS}	Drain-to-Source Voltage	12	٧	
Q_g	Gate Charge Total (4.5 V)	5.1	nC	
Q_{gd}	Gate Charge Gate-to-Drain	0.76	nC	
D	Drain-to-Source On-Resistance	V _{GS} = 2.5 V 9.1		mΩ
R _{DS(on)}	Diam-to-Source On-Resistance	V _{GS} = 4.5 V 7.5		11177
$V_{GS(th)}$	Threshold Voltage	0.8	V	

Device Information

DEVICE	MEDIA	QTY	PACKAGE	SHIP
CSD13202Q2	7-Inch Reel	3000	SON 2.00-mm × 2.00-mm Plastic Package	Tape and Reel

Absolute Maximum Ratings

T _A = 2	5°C	VALUE	UNIT						
V_{DS}	Drain-to-Source Voltage	12	٧						
V _{GS}	Gate-to-Source Voltage	±8	V						
	Continuous Drain Current (Package Limit)	22	Α						
I _D	Continuous Drain Current ⁽¹⁾	14.4							
I_{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	76	Α						
P _D	Power Dissipation ⁽¹⁾	2.7	W						
T _J , T _{STG}	Operating Junction, Storage Temperature	-55 to 150	°C						
E _{AS}	Avalanche Energy, Single Pulse $I_D = 20 \text{ A}, L = 0.1 \text{ mH}, R_G = 25 \Omega$	20	mJ						

- (1) $R_{\theta JA} = 45$ °C/W on 1-in² Cu (2-oz) on 0.06-in thick FR4 PCB.
- (2) Pulse duration 10 μs, duty cycle ≤ 2%.

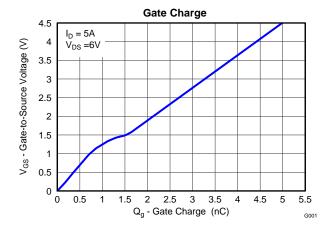




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4 Revision History

CI	hanges from Original (September 2013) to Revision A	Page
•	Added Device Information table, Specifications section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section	
•	Updated the mechanical drawings	

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5 Specifications

5.1 Electrical Characteristics

 $T_{\Delta} = 25^{\circ}C$, unless otherwise specified

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC	CHARACTERISTICS					
BV_{DSS}	Drain-to-source voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	12			V
I _{DSS}	Drain-to-source leakage current	V _{GS} = 0 V, V _{DS} = 9.6 V			1	μΑ
I _{GSS}	Gate-to-source leakage current	V _{DS} = 0 V, V _{GS} = 8 V			100	nA
V _{GS(th)}	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_{DS} = 250 \mu A$	0.58	0.80	1.10	V
		$V_{GS} = 2.5 \text{ V}, I_{DS} = 5 \text{ A}$		9.1	11.6	
R _{DS(on)}	Drain-to-source on-resistance	$V_{GS} = 3 \text{ V}, I_{DS} = 5 \text{ A}$		8.4	10.4	$m\Omega$
		$V_{GS} = 4.5 \text{ V}, I_{DS} = 5 \text{ A}$		7.5	9.3	
g _{fs}	Transconductance	V _{DS} = 6 V, I _{DS} = 5 A		44		S
DYNAMI	C CHARACTERISTICS					
C _{ISS}	Input capacitance			767	997	pF
Coss	Output capacitance	$V_{GS} = 0V, V_{DS} = 6 V, f = 1 MHz$		506	657	pF
C _{RSS}	Reverse transfer capacitance			43	56	pF
R_g	Series gate resistance			0.7	1.4	Ω
Qg	Gate charge total (4.5 V)			5.1	6.6	nC
Q_{gd}	Gate charge gate-to-drain	V _{DS} = 6 V, I _{DS} = 5 A		0.76		nC
Q_{gs}	Gate charge gate-to-source	V _{DS} = 6 V, I _{DS} = 5 A		0.98		nC
$Q_{g(th)}$	Gate charge at Vth			0.57		nC
Q_{OSS}	Output charge	V _{DS} = 6 V, V _{GS} = 0 V		5.7		nC
t _{d(on)}	Turnon delay time			4.5		ns
t _r	Rise time	$V_{DS} = 6 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{DS} = 5 \text{ A}$		28		ns
t _{d(off)}	Turnoff delay time	$R_G = 2 \Omega$		11.0		ns
t _f	Fall time			13.6		ns
DIODE C	HARACTERISTICS	· · ·				
V _{SD}	Diode forward voltage	I _{DS} = 5 A, V _{GS} = 0 V		0.75	1	V
Q _{rr}	Reverse recovery charge	V = 6 V = 5 A di/dt = 200 A/vs		13		nC
t _{rr}	Reverse recovery time	$V_{DD} = 6 \text{ V}, I_F = 5 \text{ A}, \text{ di/dt} = 200 \text{ A/}\mu\text{s}$		28		ns

5.2 Thermal Characteristics

 $T_A = 25$ °C unless otherwise stated

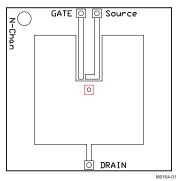
	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal resistance junction-to-case ⁽¹⁾			6.4	°C/W
$R_{\theta JA}$	Thermal resistance junction-to-ambient (1)(2)			60	°C/W

 ⁽¹⁾ R_{θ,JC} is determined with the device mounted on a 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu pad on a 1.5-in x 1.5-in (3.81-cm x 3.81-cm), 0.06-in (1.52-mm) thick FR4 PCB. R_{θ,JC} is specified by design, whereas R_{θ,JA} is determined by the user's board design.
 (2) Device mounted on FR4 material with 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu.

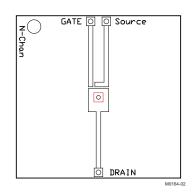
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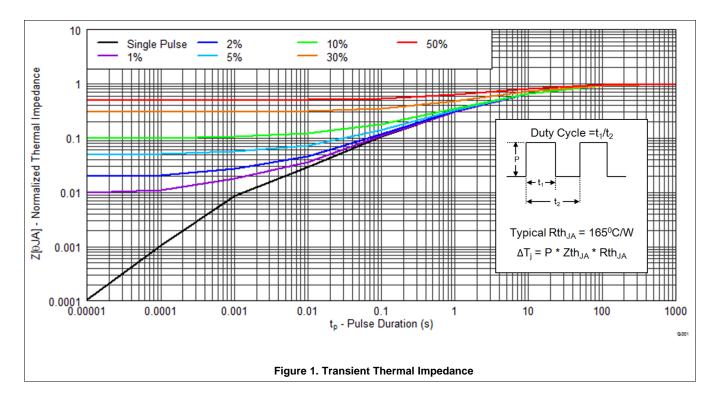
Max $R_{\theta JA} = 60$ when mounted on 1 in² (6.45 cm²) of 2-oz (0.071-mm) thick Cu.



Max $R_{\theta JA} = 210$ when mounted on minimum pad area of 2-oz (0.071-mm) thick Cu.

5.3 Typical MOSFET Characteristics

T_A = 25°C unless otherwise stated

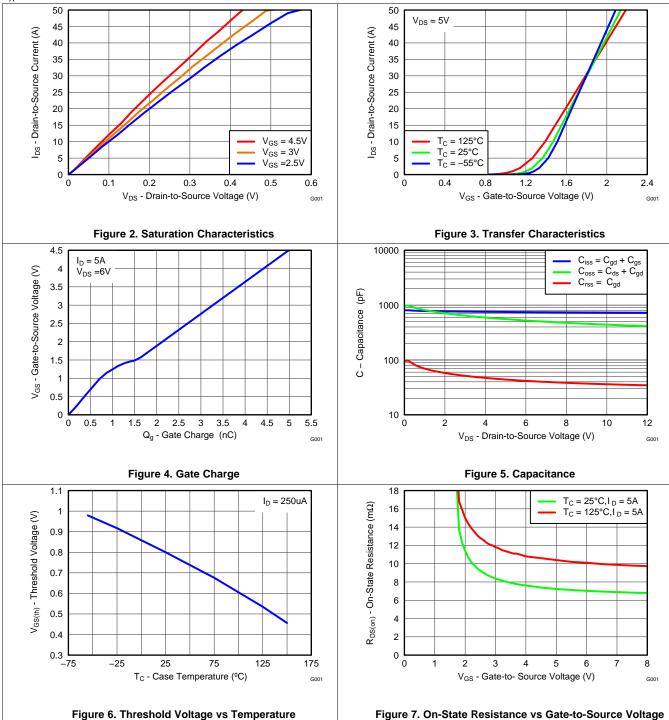


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Typical MOSFET Characteristics (continued)

 $T_A = 25$ °C unless otherwise stated





Typical MOSFET Characteristics (continued)

 $T_A = 25$ °C unless otherwise stated

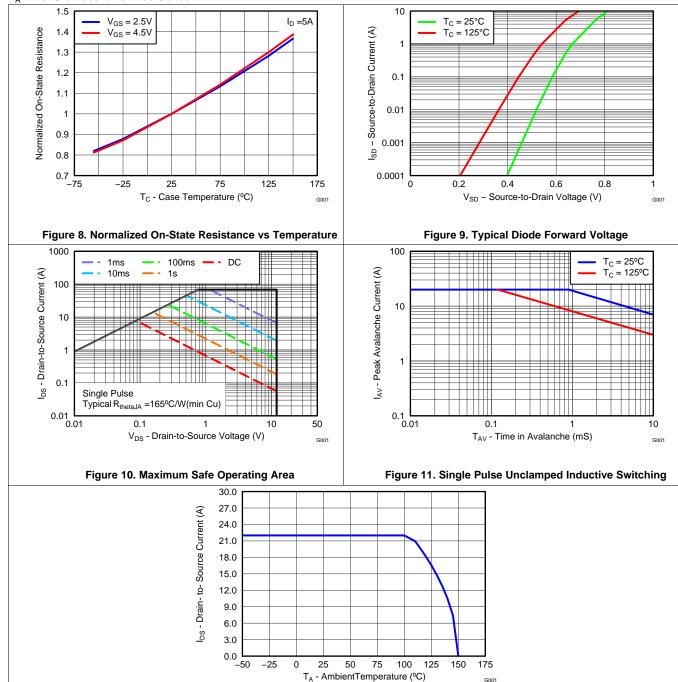


Figure 12. Maximum Drain Current vs Temperature



6 Device and Documentation Support

6.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

6.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

6.3 Trademarks

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6.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

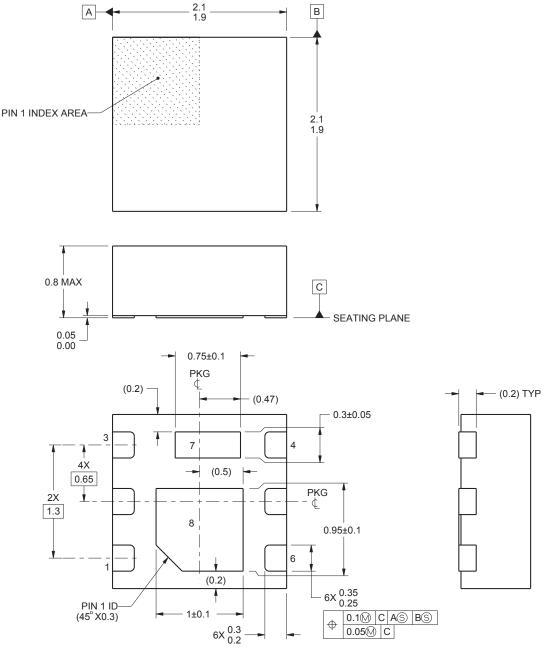
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7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 Q2 Package Dimensions



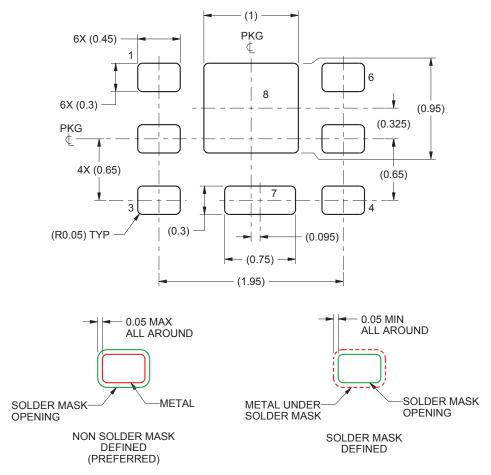
- 4222322/A 08/2015
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pads must be soldered to the printed circuit board for thermal and mechanical performance.

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Q2 Package Dimensions (continued)

7.1.1 Recommended PCB Pattern



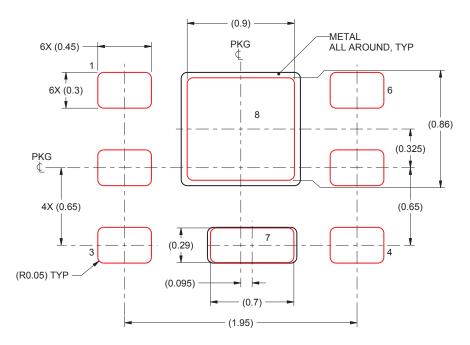
SOLDER MASK DETAILS

1. This package is designed to be soldered to a thermal pad on the board. For more information, see *QFN/SON PCB Attachment* (SLUA271).



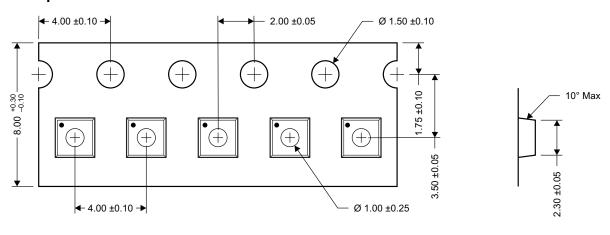
Q2 Package Dimensions (continued)

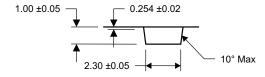
7.1.2 Recommended Stencil Pattern



1. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

7.2 Q2 Tape and Reel Information





M0168-01

Notes: 1. Measured from centerline of sprocket hole to centerline of pocket.

- 2. Cumulative tolerance of 10 sprocket holes is ±0.2.
- 3. Other material available.
- 4. Typical SR of form tape max 10^9 OHM/SQ.
- 5. All dimensions are in mm, unless otherwise specified.

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www.ti.com 10-Nov-2025

PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
CSD13202Q2	Active	Production	WSON (DQK) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 150	1322
CSD13202Q2.B	Active	Production	WSON (DQK) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 150	1322
CSD13202Q2G4.B	Active	Production	WSON (DQK) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 150	1322

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

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